Patent number:

WO0239495

Publication date:

2002-05-16

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Classification:

- international:

H01L21/3065; H01L21/31; H01L21/205

- european:

H01J37/32D; H01L21/00S2D8D

Application number: WO2001JP09923 20011113 Priority number(s): JP20000345008 20001113

Also published as:

US2004035364 (A1) JP2002151473 (A)

Cited documents:

JP2001057361 JP63253628

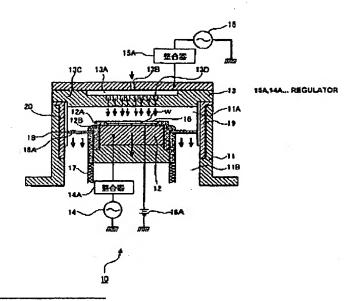
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JP8045907

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Abstract of WO0239495

A plasma processing device, comprising a lower electrode (12) for supporting a wafer (W) inside a chamber (11), a shielding member (19) for shielding the inner peripheral surface of the chamber (11) from the plasma for processing the wafer (W), and a baffle plate (18) disposed in a space between the shielding member (19) and the lower electrode (12) and dispersedly discharging the gas inside the chamber (11), wherein a resin plate (20) is replaceably installed on the inner peripheral surface of the shielding member (19), and a compressive pressure in circumferential direction is provided to the resin plate (20).



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